
About this product

Features & Benefits

- Developed according to ISO 26262, compliant with the requirements of ASIL B(D)
- Low jitter 0.02% due to high switching accuracy enables iTPMS
- Two-wire current interface 7mA/14mA providing speed information
- Wide operating junction temperature range -40°C to 190°C
- Robustness against external magnetic disturbances up to 2mT through differential sensing principle
- High sensitivity enables outstanding air gap performance along with immunity against y-displacement effects
- Small sensor package 5x3mm without need of external capacitor saves module size, increases robustness against mechanical stress, and enables design freedom
- Advanced EMC concept maximizes the availability of the sensor signal
- New established Micro Break feature designed to be immune against disturbances on supply line

Order Information

Table 1

Type	Description	Ordering Number
TLE5045iC-R050	Speed only sensor optimized for use with load resistor $R_m \leq 50 \Omega$	SP001649080
TLE5045iC-R100	Speed only sensor optimized for use with load resistor $50 \Omega \leq R_m \leq 100 \Omega$	SP001216864

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1 Product Characteristics

1 Product Characteristics

Absolute Maximum Ratings

Stresses above the maximum values listed here may cause permanent damage to the device.

Table 2

Parameter	Symbol	Min.	Typ.	Max.	Unit	Note / Test Condition
Supply voltage	V_{DD}	-	-	24	V	max. 30 min @ $T_J = 25 \pm 5^\circ\text{C}$
		-0.6	-	-	V	$T_J < 80^\circ\text{C}$, I_{DD} reverse current limit applies
Reverse current	I_{DD}	-200	-	-	mA	t = max 4 h
Junction temperature	T_J	-40	-	190	$^\circ\text{C}$	max 4 h, < 16.5 V
Magnetic flux density	B_{max_x}	-	-	250	mT	max. 1min @ $T_A \leq 85^\circ\text{C}$
	B_{max_y}	-	-			
	B_{max_z}	-	-	500	mT	max. 1min @ $T_A \leq 85^\circ\text{C}$

Operating Range

The following operating conditions must not be exceeded in order to ensure correct operation.

Table 3

Parameter	Symbol	Min.	Typ.	Max.	Unit	Note / Test Condition
Supply voltage	V_{DD}	5.2	-	20	V	TLE5045iC-R100
	V_{DD}	4.25	-	20	V	TLE5045iC-R050
Operating Temperature	T_J	-40		190	$^\circ\text{C}$	
Magnetic signal frequency	f_{mag}	0.03	-	3000	Hz	
Minimum differential magnetic input signal amplitude, magnetic encoder application	$\text{dB}_{\text{limit}_x}$ $T_A = 25^\circ\text{C}$	70	90	110	μT	99% criterium
Magnetic induction amplitude at each GMR sensing element	B_x	-25	-	25	mT	
Dynamic and static homogeneous external disturbance fields	$B_{\text{ext}_{XYZ}}$	-2		2	mT	no unwanted pulses

1 Product Characteristics

Functional Parameters

The magnetic input is assumed sinusoidal with constant amplitude and offset. The typical values shown below are valid for $V_{DD} = 12\text{ V}$ and $T_A = 25^\circ\text{C}$. For a more detailed specification please refer to our product datasheets which are available on request.

Table 4

Parameter	Symbol	Min.	Typ.	Max.	Unit	Note / Test Condition
Period jitter	S_{jit}	-	± 0.02		%	$\pm 1\sigma$ value
Duty cycle	DC	40	-	60	%	in calibrated mode
Supply current during static output low state	I_{low}	5.95	7	8.05	mA	
Supply current during static output high state	I_{high}	11.9	14	16.1	mA	
Current level for indicating errors	I_{Error}	1	3.5	3.8	mA	
Output current slew rate	SR_r, SR_f	11	-	28	mA/ μs	$SR_r = (I_{90\%} - I_{10\%}) / t_r$ $SR_f = (I_{90\%} - I_{10\%}) / t_f$
Switch-off voltage	V_{reset}			3.5	V	direct on sensor pins
Supply voltage hysteresis	V_{Hys}	1.5		1.7	V	TLE5045iC-R100
Supply voltage hysteresis	V_{Hys}	0.65		0.75	V	TLE5045iC-R050

2 Functional Description

2 Functional Description

The sensor element has a magnetic interface to detect the increments of a magnetized encoder: the sensing principle is based on the giant magneto resistance (GMR) principle sensitive to magnetic fields in x-direction. It is designed for maximum sensitivity and suppression of homogeneous fields.

In the figure below the typical placement of the TLE5045iC facing a magnetic encoder wheel is shown. The figure also indicates the coordinate system, which is valid throughout this document.

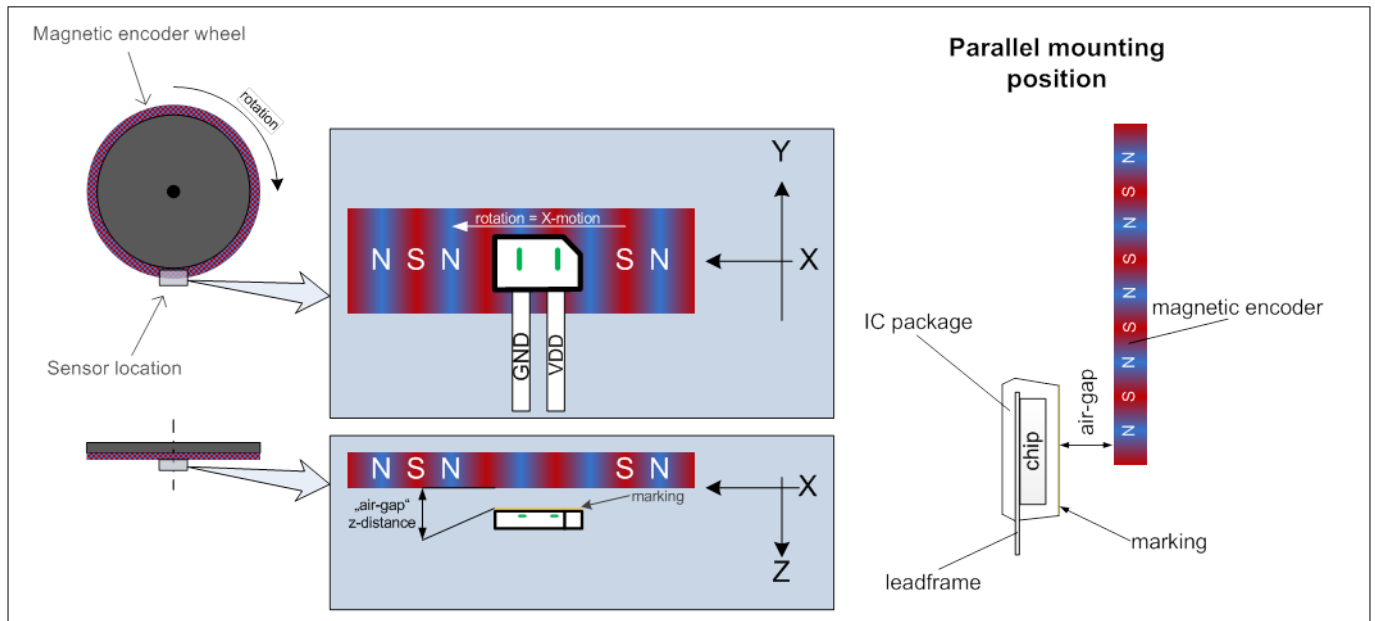


Figure 2 Typical placement of the TLE5045iC

3 Speed Protocol

3 Speed Protocol

The first output pulse is generated when the input field exceeds the minimal magnetic threshold $2 \times dB_{limit}$. After minimum and maximum are detected and offset is compensated, output switching occurs at zerocrossing of the differential magnetic signal.

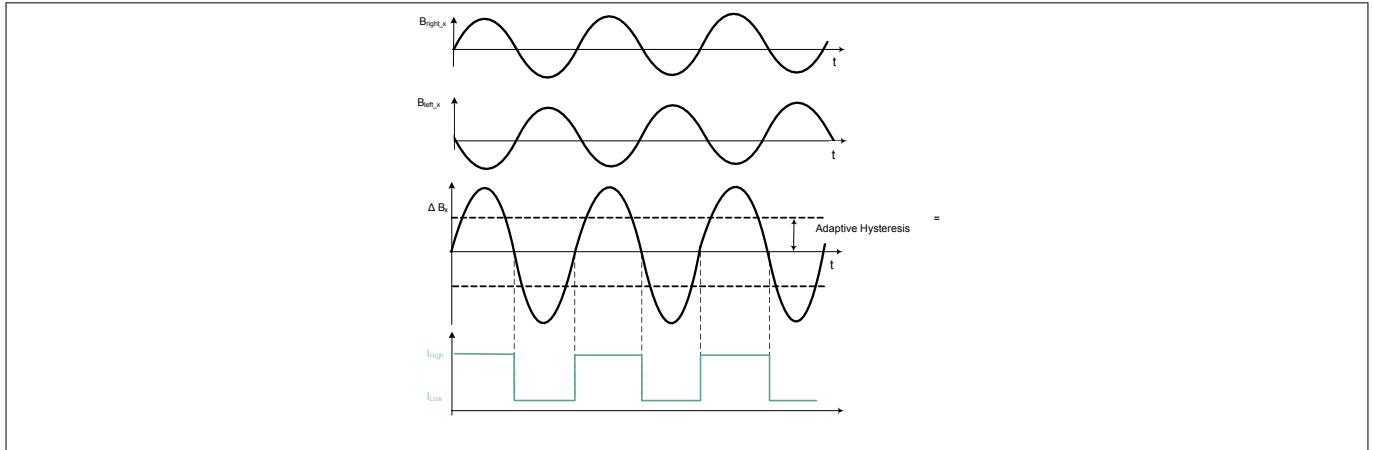


Figure 3 **Signal output pulse**

4 Safety Mechanisms

The TLE5045iC offers safety features to support the Automotive Safety Integrity Level ASIL B and is designed to be used in ASIL D systems.

An embedded safety concept was developed to notify the Control System in case of an internal error by setting the output current level to a constant failure indication level I_{Error} .

Following safety mechanisms have been implemented:

- **Undervoltage detection:** This safety mechanism detects voltage drops to values where the correct functionality of the circuitry is no more ensured. The sensor remains in this state until the error condition is solved and V_{DD} is back into normal operating range.
- **Detection of discrepancy between number of active fuses and internally stored number of fuses:** This safety mechanism compares the active fuse bits against the internal stored quantity. The sensor remains in this failure indication state I_{Error} until the device is powered off and on again and the error condition is not present any longer.

The entirety of Infineon experience has been used to identify and prevent common cause of failure in the application including EMC disturbances and mechanical tolerances. An advanced EMC concept, inclusive of microbreak feature, without the need of external components, maximizes the availability of the sensor signal at the electrical interface. Also, the speed algorithm is designed for fast start-up and optimization of duty cycle. The extremely low jitter of the sensor contributes to high time accuracy of the speed signal.

TLE5045iC is accompanied by accurate safety analysis and complete documentation to enable the system integrator to quickly evaluate the compatibility with the system/item and start the integration process. A detailed description of how the sensor is to be used in an ISO26262 compliant system can be found in the Safety Manual and Safety Analysis Summary Report, which are available on request.

5 ESD and EMC Characteristics

The TLE5045iC is characterized according to the IC level EMC requirements described in the "Generic IC EMC Test Specification" Version 2.0 from 2014. EMC testreport is available on request.

6 ESD HBM Model

Additionally component level EMC characterizations are performed according to ISO 7637-2:2011, ISO 7637-3:2007 and ISO 16750-2:2010 regarding pulse immunity, and CISPR 25 (2009-01) Ed. 3.0 regarding conducted emissions.

6 ESD HBM Model

Table 5

Parameter	Symbol	Min.	Typ.	Max.	Unit	Note / Test Condition
ESD Voltage	V_{HBM}	-	-	± 12	kV	Method AEC-Q100 Rev H (1.5 k Ω , 100 pF)

7 Product Qualification

Product qualification according to AEC-Q100 Grade 0 is performed.

8 Pin Configuration

Table 6

Pin No.	Symbol	Function
1	VDD	Supply voltage
2	GND	Ground

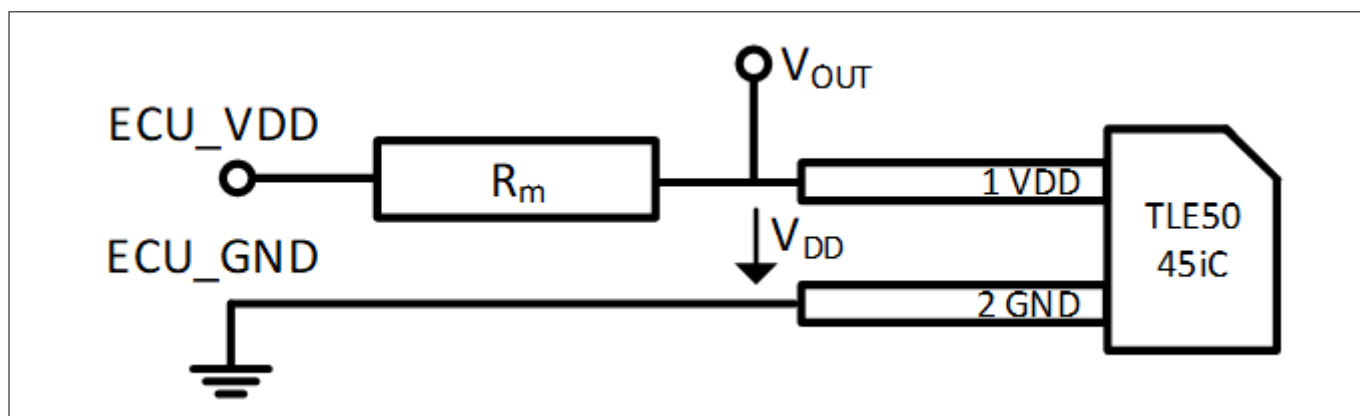


Figure 4 Pin configuration



10 Terminology

10 Terminology

Table 7

μs	microsecond
μT	micro-Tesla
A	Ampere
AEC	Automotive Electronics Council
AK	Arbeitskreis
ASIC	application specific integrated circuit
ASIL	automotive safety integrity Level
C	Celsius
CISP	Comité international spécial des perturbations radioélectriques
EMC	electromagnetic compatibility
ESD	electrostatic discharge
GMR	giant magneto resistance
GND	ground
h	hour
HBM	human body model
Hz	Hertz
IC	integrated circuit
iGMR	integrated giant magneto resistance
ISO	International Organization for Standardization
iTPMS	integrated tire pressure monitoring system
kΩ	kilo-Ohm
kV	kilo-Volt
mA	milli-Ampere
min	minute
mm	millimeter
ms	millisecond
mT	milli-Tesla
Ω	Ohm
pF	picoFarad
PWM	pulse width modulation
V	Volt
VDD	supply voltage

Revision history

Revision history

Document version	Date of release	Description of changes
1.0	2018-11-06	Initial version

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Edition 2018-11-06

Published by
Infineon Technologies AG
81726 Munich, Germany

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Document reference
IFX-srj1538755497187

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